1763#2  
PATENT

Case Docket No. ASMJP.090AUS

Date: January 11, 2002  
155  
12-1-03  
RST/SL

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Todd, et al.  
Appl. No. : 09/993,024  
Filed : November 13, 2001  
For : LOW-K DIELECTRIC  
MATERIALS AND  
PROCESSES  
Examiner : Unknown  
Group Art Unit : 1763

I hereby certify that this correspondence and all  
marked attachments are being deposited with the  
United States Postal Service as first class mail in an  
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January 11, 2002

(Date)

Joseph J. Mallon Reg. No. 39,287

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## TRANSMITTAL LETTER

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231  
ATTENTION: APPLICATION BRANCH

Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) An Information Disclosure Statement.
- (X) A PTO Form 1449 with Sixty-seven (67) references.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.

Joseph J. Mallon  
Joseph J. Mallon  
Registration No. 39,287  
Attorney of Record



ASMJP.090AUS

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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Enclosed is form PTO-1449 listing references that are also enclosed. This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

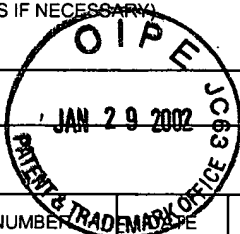
Dated: 1/11/02

By: Joseph J. Mallon  
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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMJP.090AUSAPPLICATION NO.  
09/993,024INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT  
Todd, et al.FILING DATE  
November 13, 2001GROUP  
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## U.S. PATENT DOCUMENTS

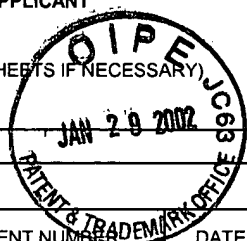
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,781,942	11/01/88	Leyden et al.			
	2.	4,863,755	09/05/89	Hess et al.			
	3.	4,894,352	01/16/90	Lane et al.			
	4.	4,992,306	02/12/91	Hochberg et al.			
	5.	5,011,706	04/30/91	Tarhay et al.			
	6.	5,028,566	07/02/91	Lagendijk			
	7.	5,231,058	07/27/93	Maeda et al.			
	8.	5,240,813	08/31/93	Watanabe et al.			
	9.	5,244,698	09/14/93	Ishihara et al.			
	10.	5,314,724	05/24/94	Tsukune et al.			
	11.	5,324,539	06/28/94	Maeda et al.			
	12.	5,380,555	01/10/95	Mine et al.			
	13.	5,433,786	07/18/95	Hu et al.			
	14.	5,494,712	02/27/96	Hu et al.			
	15.	5,554,570	09/10/96	Maeda et al.			
	16.	5,563,105	10/08/96	Dobuzinsky et al.			
	17.	5,703,404	12/30/97	Matsuura			
	18.	5,840,821	11/24/98	Nakano et al.			
	19.	5,876,798	03/02/99	Vassiliev			
	20.	5,989,998	11/23/99	Sugahara et al.			
	21.	5,998,522	12/07/99	Nakano et al.			
	22.	6,045,877	04/04/00	Gleason et al.			
	23.	6,051,321	04/18/00	Lee et al.			
	24.	6,051,508	04/18/00	Takase et al.			
	25.	6,054,379	04/25/00	Yau et al.			
	26.	6,068,884	05/30/00	Rose et al.			

EXAMINER

DATE CONSIDERED

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMJP.090AUS	APPLICATION NO. 09/993,024
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Todd, et al.	
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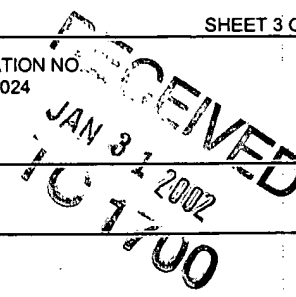
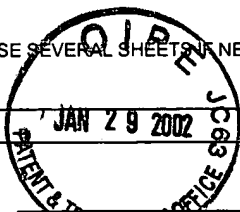
## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	27.	WO 97/41592	11/06/1997	PCT				
	28.	WO 97/40207	10/30/97	PCT				
	29.	WO 99/55526	11/04/99	PCT				
	30.	WO 99/60621	11/25/1999	PCT				
	31.	WO 99/41423	08/19/1999	PCT				
	32.	WO 99/21706	05/06/1999	PCT				
	33.	EPO 367 004 B1	12/15/93	EPO				
	34.	EP 0 436 185 B1	03/20/96	EPO				
	35.	EP 0 723 600 B1	07/07/99	EPO				
	36.	EP 0 771 886 A1	05/07/97	EPO				
	37.	EP 0 935 283 A2	08/11/99	EPO				
	38.	EP 0 960 958 A2	12/01/99	EPO				
	39.	EP 0 706 216 A2	04/10/1996	EPO				
	40.	JP 09293716	11/11/97	JP (Abstract only)			X	
	41.	JP 11176829	07/02/99	JP (Abstract only)			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	42.	Bayer et al., <i>Overall kinetics of SiO<sub>x</sub> remote-PECVD using different organosilicon monomers</i> , Surface and Coatings Technology, 116-119 (1999) 874-878
	43.	Berjoan et al., <i>XPS and XPS valence band characterizations of amorphous or polymeric silicon based thin films prepared by PACVD from organosilicon monomers</i> , J. Phys. IV France 9 (1999) pp. 1059-1068.
	44.	Constant et al., <i>Some Properties of amorphous SiXC<sub>1-x</sub> (H) alloys prepared by CVD from various organosilicon compounds</i> , Solid State Chemistry, 1982, pp. 267-270
	45.	Deville et al., <i>An AES study of the influence of carbon on the chemical structure of some oxide films deposited by PECVD of organosilicon precursors</i> , Applied Surface Science 137 (1999) 136-141
	46.	Fonseca et al., <i>Plasma Polymerization of Tetramethylsilane</i> , Am. Chemical Society, 1993, 5, 1676-1682
	47.	Inoue et al., <i>Mass spectroscopy in plasma-enhanced chemical vapor deposition of silicon-oxide films using tetramethoxysilane</i> , Thin Solid Films 316 (1998) 79-84
	48.	Inoue et al., <i>Spectroscopic studies on preparation of silicon oxide films by PECVD using organosilicon compounds</i> , Plasma Sources Sci. Technol. 5 (1996) 339-343
	49.	Loboda, M.J., <i>New solutions for intermetal dielectrics using trimethylsilane-based PECVD processes</i> , Microelectronic Engineering 50 (2000) 15-23
	50.	Nguyen et al., <i>Plasma organosilicon polymers</i> , J. Electrochem. Soc., August 1985, pp. 1925-1932

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51.	Shirafuji et al., <i>PECVD of Fluorocarbon/SiO composite thin films using C4F8 and HMDSO</i> , Plasmas and Polymers, Vo. 4, No. 1, 1999, pp. 57-75
52.	Shirafuji et al., <i>PE-CVD of fluorocarbon/silicon oxide composite thin films from TFE and HMDSO</i> , Mat. Res. Soc. Symp. Proc. Vol. 544, pp. 173-178
53.	Shirafuji et al., <i>Plasma copolymerization of tetrafluoroethylene/hexamethyldisiloxane and In Situ Fourier Transform infrared spectroscopy of its gas phase</i> , Jpn. J. Appl. Phys. Vol. 38 (1999) pp. 4520-4526
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56.	Matsuki, N., U.S. Patent Application No. 09/243,156 <i>Silicone Polymer insulation film on semiconductor substrate and method for forming the film</i> , filed February 2, 1999.
57.	Indrajit Banerjee, et al., "Characterization of Chemical Vapor Deposited Amorphous Fluorocarbons for Low Dielectric Constant Interlayer Dielectrics." J. Electrochem. Soc., Vol. 146(6), p. 2219 (1999).
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64.	Savage, Charles R., et al., "Spectroscopic Characterization of Films Obtained in Pulsed Radio-Frequency Plasma Discharges of Fluorocarbon Monomers," Structure-Property Relations in Polymers, pp. 745-768, American Chemical Society, (1993).
65.	Sharp, K.G., et al., "Perfluoro(alkylsilanes). II: Trifluoro(trifluoromethyl) silane and Trifluoro(pentafluoroethyl) silane," Inorg. Chem., Vol. 11, No. 6, pp. 1259-1264, (1972).
66.	Pam Frost Gorder, "Researchers Pioneer Reqniques to Lubicate Microdevices," Research News, Ohio State University, <a href="http://www.acs.ohio-state.edu/units/research">http://www.acs.ohio-state.edu/units/research</a> , (3/23/01).
67.	Chandrasekhar et al., "New Silicon-Carbon Materials Incorporating Si4C Building Blocks" Mat. Res. Soc. Symp. Proc. Vol. 441, Materials Research Society (1997)

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